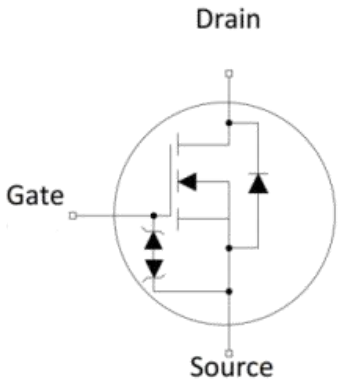
VSTJ065R20BNA

Datasheet

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
650V	2000mΩ@10V	3.5A

Symbol

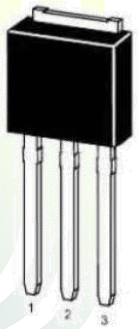


Symbol of VSTJ065R20BNA

Features

- Low RDS(on) & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Integrated ESD protection diode

Package Type



TO-251

Package Type of VSTJ065R20BNA

Application

- PC power
- Telecom power
- Server power
- EV Charger
- Motor driver

Ordering Information

Product Name	Package	Marking
VSTJ065R20BNA	TO-251	STJ065R20BNA

Absolute Maximum Ratings (T_J= 25 ºC, unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current Note 1	T_C=25ºC	I_D	3.5	A
Pulsed Drain Current Note 2	T_C=25ºC	$I_{D, pulse}$	10.5	A
Continuous Diode Forward Current Note 1	T_C=25ºC	I_S	3.5	A
Diode Pulsed Current Note 2	T_C=25ºC	$I_{S, pulse}$	10.5	A
Max Power Dissipation Note 3	T_C=25ºC	P_D	60	W
Avalanche Current, Single Pulse Note 4		I_{AS}	1.8	A
Avalanche Energy, Single Pulse Note4		E_{AS}	97	mJ
Gate source ESD(HBM-C=100pF, R=1.5kΩ)		$V_{ESD(G-S)}$	Class 2	-
MOSFET dv/dt ruggedness, V_{DS}=0~480V		dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS}=0~480V, I_{SD}<= I_D		dv/dt	15	V/ns
Operation and storage temperature		T_J,T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{θJC}$	-	2.08	-	ºC/W
Thermal Resistance, Junction-to-Ambient Note5	$R_{θJA}$	-	62.5	-	

Notes:

Note1: Calculated continuous current based on maximum allowable junction temperature.

Note2: Pulse width limited by safe operating area.

Note3: Based on max. junction temperature, using junction-case thermal resistance.

Note4: V_{DD}=100V, V_{GS}=10V, L=60mH, starting T_A=25 °C.

Note5: When mounted on 1 inch square copper board, t≤10sec. The value in any given application depends on the user's specific board design.

Electrical Characteristics (T_J= 25 ºC, unless otherwise specified)

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250uA	650	-	-	V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=650V, V_{GS}=0V	-	-	1	uA
Gate-Source Leakage Current	Forward	I_{GSSF}	V_{GS}=30V, V_{DS}=0V	-	-	1	uA
	Reverse	I_{GSSR}	V_{GS}=-30V, V_{DS}=0V	-	-	-1	
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250uA	3.0	4.0	5.0	V
Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=2.5A	-	1638	2000	mΩ
Gate Resistance		R_G	F=1MHz, Open Drain	-	21.2	-	Ω
Dynamic Characteristics							
Input Capacitance		C_{iss}	V_{DS}=50V	-	196	-	pF
Output Capacitance		C_{oss}	V_{GS}=0V	-	23	-	pF
Reverse Transfer Capacitance		C_{rss}	f=1MHz	-	0.84	-	pF
Turn-on Delay Time		$t_{d(on)}$	V_{DS}=380V	-	6.1	-	ns
Rise Time		t_r	I_D=5A	-	16.1	-	
Turn-off Delay Time		$t_{d(off)}$	R_G=25Ω	-	13.9	-	
Fall Time		t_f	V_{GS}=10V	-	14.2	-	
Gate Charge Characteristics							
Gate to Source Charge		Q_{gs}	V_{DS}=400V	-	1.95	-	nC
Gate to Drain Charge		Q_{gd}	I_D=5A	-	1.83	-	
Gate Charge Total		Q_g	V_{GS}=0 to 10V	-	4.83	-	
Gate Plateau Voltage		$V_{Plateau}$		-	6.05	-	V
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS}=0V, I_S=1A	-	0.8	1.5	V
Reverse Recovery Time		t_{rr}	V_R=400V	-	235	-	ns
Reverse Recovery Charge		Q_{rr}	I_S=5A	-	1120	-	nC
Peak Reverse Recovery Current		I_{rrm}	di/dt=100A/us	-	8.26	-	A

Electrical Characteristics Diagrams

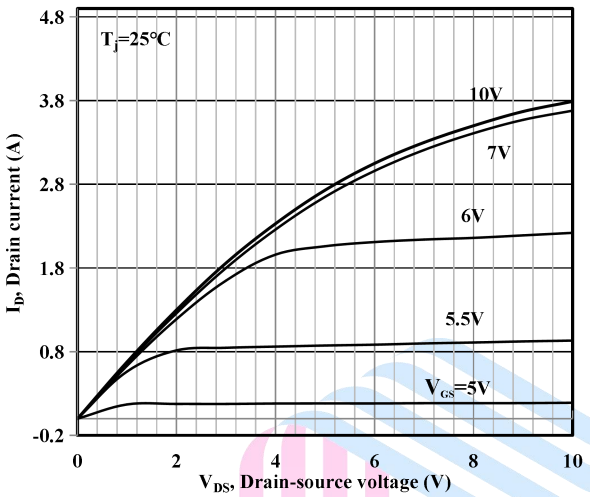


Figure 1. Typ. output characteristics

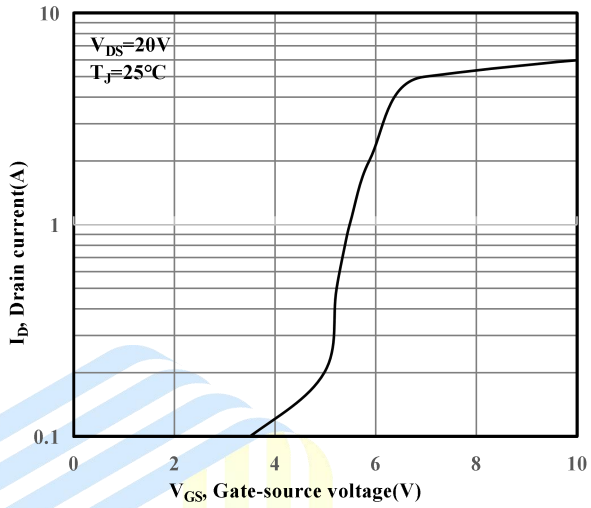


Figure 2. Typ. transfer characteristics

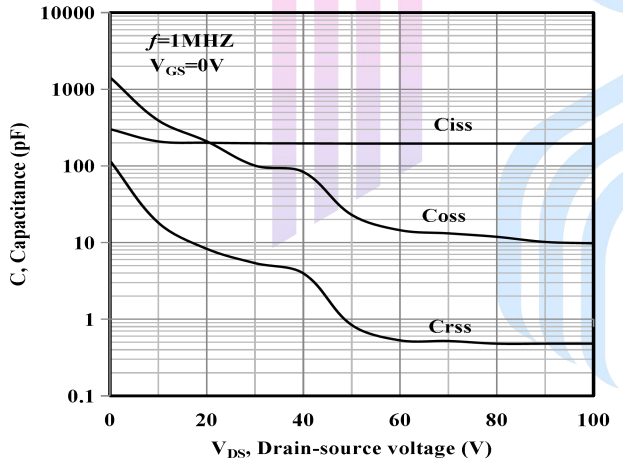


Figure 3. Typ. capacitances

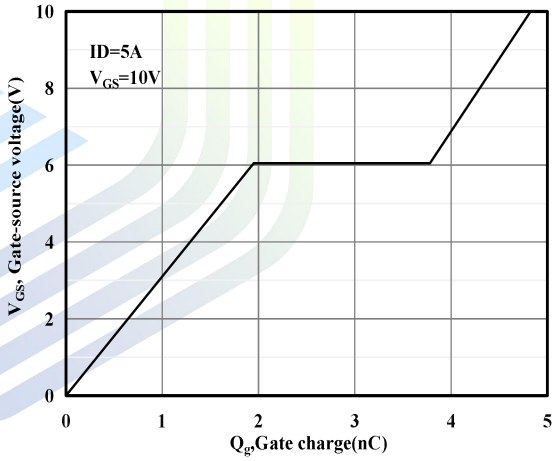


Figure 4. Typ. gate charge

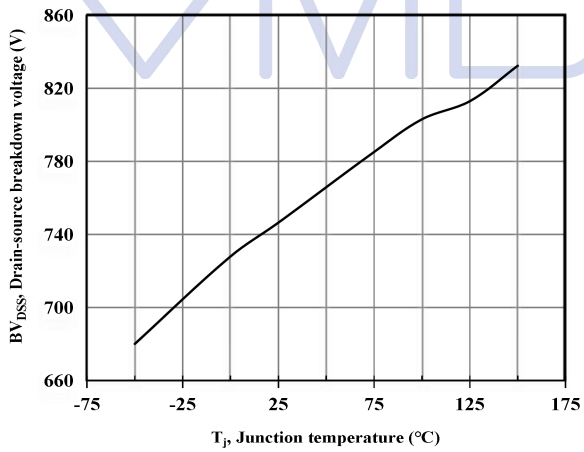


Figure 5. Drain-source breakdown voltage

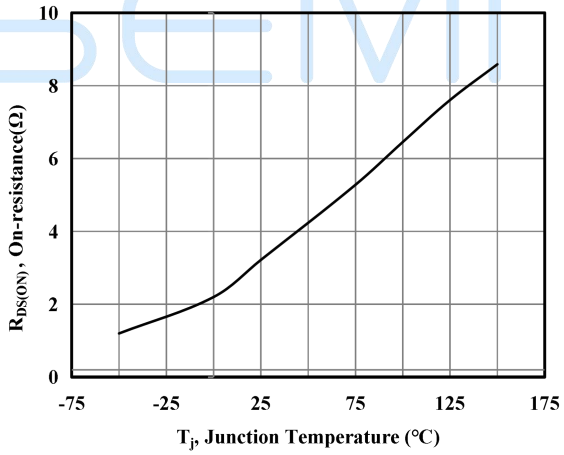


Figure 6. Drain-source on-state resistance

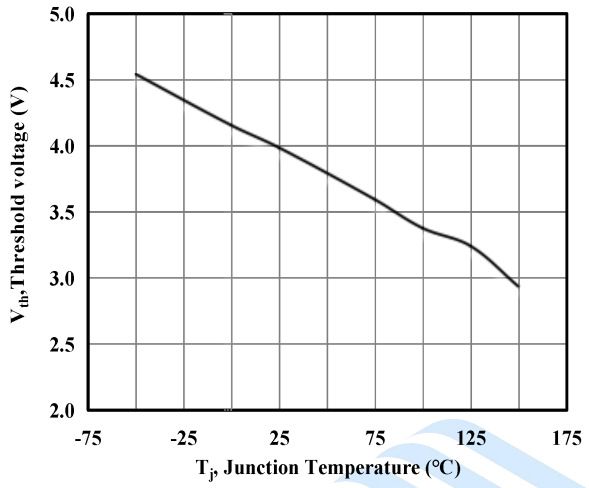


Figure 7. Threshold voltage

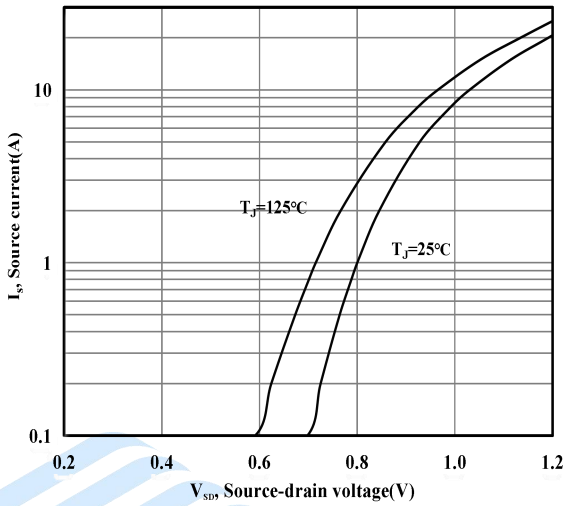


Figure 8. Forward characteristic of body diode

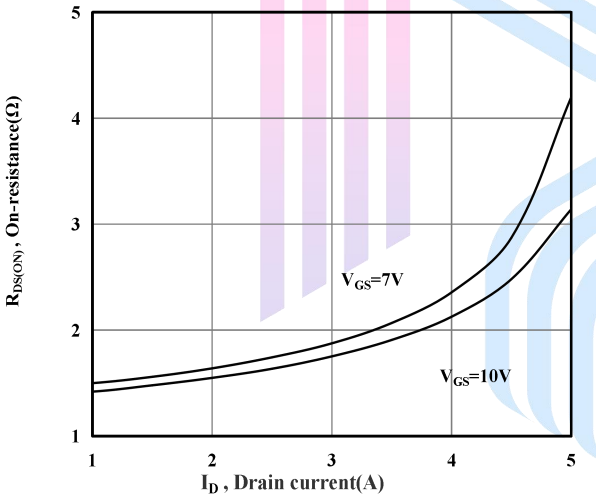


Figure 9. Drain-source on-state resistance

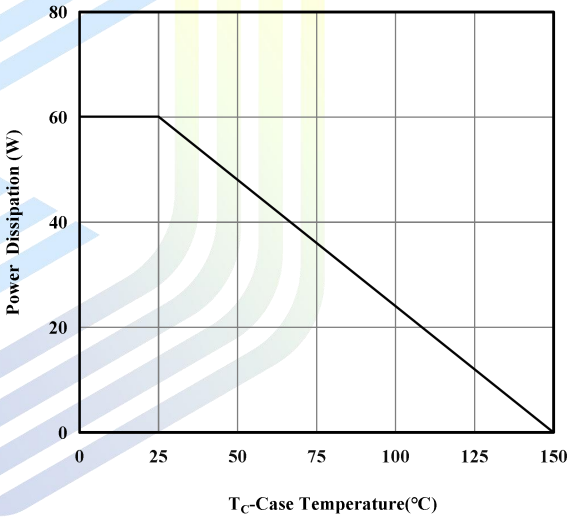


Figure 10. Power dissipation

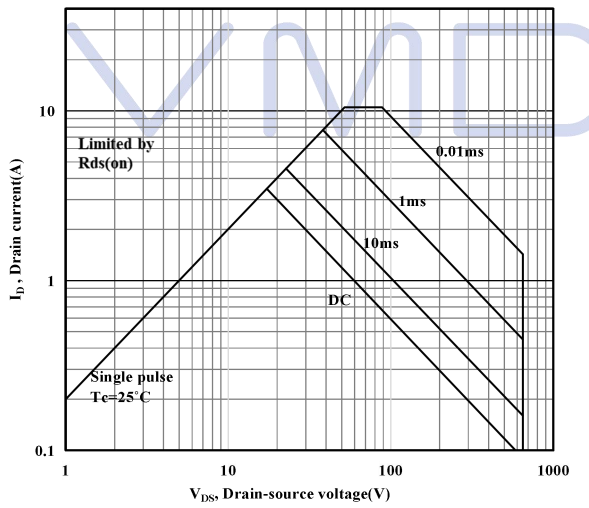


Figure 11. Safe operation area T_C=25℃

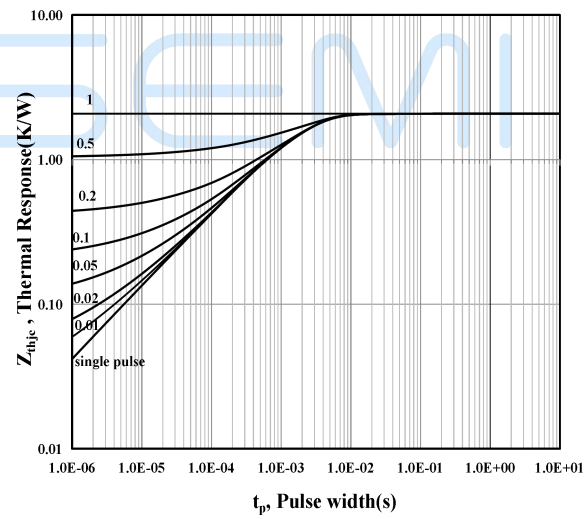
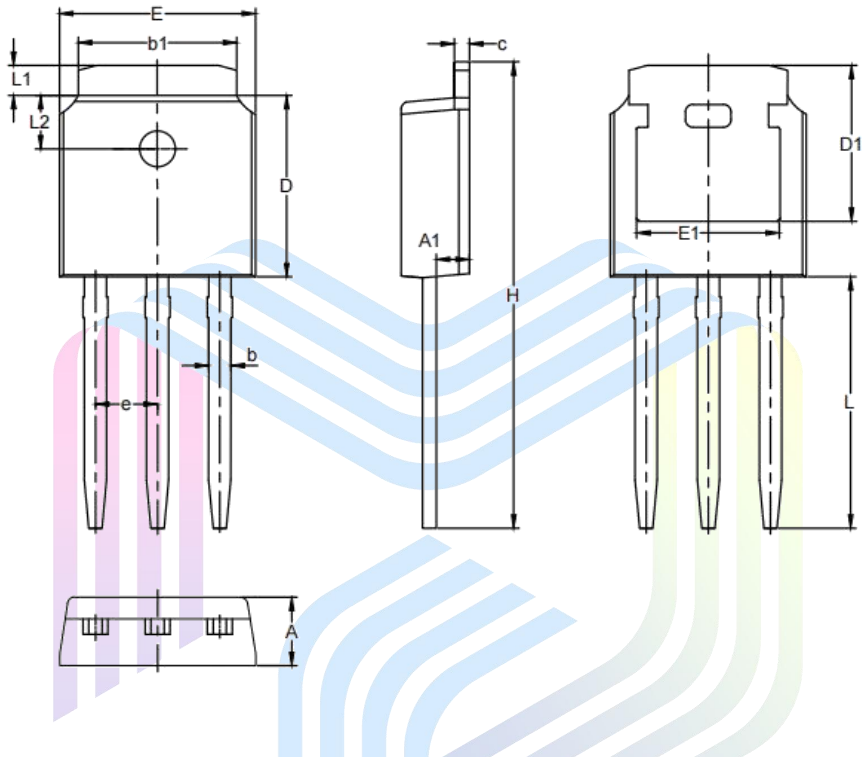


Figure 12. Max. transient thermal impedance

Mechanical Dimensions

TO-251 Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

Symbol	MIN	MAX
A	2.2	2.4
A1	0.97	1.27
b	0.6	0.9
b1	5.1	5.5
c	0.43	0.61
D	5.95	6.25
D1	5.3REF	
E	6.4	6.75
E1	4.63	-
e	2.286BSC	
H	15.9	16.9
L	9	9.65
L1	0.88	1.28
L2	1.65	1.95

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